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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1584
Total RAM Bits	18432
Number of I/O	157
Number of Gates	60000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	289-TFBGA, CSBGA
Supplier Device Package	289-CSP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp060v2-cs289i

Each I/O module contains several input, output, and output enable registers.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

IGLOO PLUS devices support JEDEC-defined wide range I/O operation. IGLOO PLUS devices support both the JESD8-B specification, covering 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V, and JESD8-12 with its 1.2 V nominal, supporting an effective operating range of 1.14 V to 1.575 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the [FlashPro User's Guide](#) for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify ([Figure 1-4 on page 1-8](#)).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

1 – I/O is set to drive out logic High

0 – I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming Z -Tri-State: I/O is tristated

Power per I/O Pin

Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings

	VCCI (V)	Dynamic Power PAC9 (μW/MHz) ¹
Single-Ended		
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	16.26
3.3 V LVTTTL / 3.3 V LVCMOS – Schmitt Trigger	3.3	18.95
3.3 V LVCMOS Wide Range ²	3.3	16.26
3.3 V LVCMOS Wide Range ² – Schmitt Trigger	3.3	18.95
2.5 V LVCMOS	2.5	4.59
2.5 V LVCMOS – Schmitt Trigger	2.5	6.01
1.8 V LVCMOS	1.8	1.61
1.8 V LVCMOS – Schmitt Trigger	1.8	1.70
1.5 V LVCMOS (JESD8-11)	1.5	0.96
1.5 V LVCMOS (JESD8-11) – Schmitt Trigger	1.5	0.90
1.2 V LVCMOS ³	1.2	0.55
1.2 V LVCMOS ³ – Schmitt Trigger	1.2	0.47
1.2 V LVCMOS Wide Range ³	1.2	0.55
1.2 V LVCMOS Wide Range ³ – Schmitt Trigger	1.2	0.47

Notes:

1. PAC9 is the total dynamic power measured on VCCI.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. Applicable for IGLOO PLUS V2 devices only, operating at VCCI ≥ VCC.

Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹

	C _{LOAD} (pF)	VCCI (V)	Dynamic Power PAC10 (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	5	3.3	127.11
3.3 V LVCMOS Wide Range ³	5	3.3	127.11
2.5 V LVCMOS	5	2.5	70.71
1.8 V LVCMOS	5	1.8	35.57
1.5 V LVCMOS (JESD8-11)	5	1.5	24.30
1.2 V LVCMOS ⁴	5	1.2	15.22
1.2 V LVCMOS Wide Range ⁴	5	1.2	15.22

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PAC10 is the total dynamic power measured on VCCI.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
4. Applicable for IGLOO PLUS V2 devices only, operating at VCCI ≥ VCC.

Power Consumption of Various Internal Resources

Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO PLUS Devices For IGLOO PLUS V2 or V5 Devices, 1.5 V Core Supply Voltage

Parameter	Definition	Device Specific Dynamic Power (μW/MHz)		
		AGLP125	AGLP060	AGLP030
PAC1	Clock contribution of a Global Rib	4.489	2.696	0.000 ¹
PAC2	Clock contribution of a Global Spine	1.991	1.962	3.499
PAC3	Clock contribution of a VersaTile row	1.510	1.523	1.537
PAC4	Clock contribution of a VersaTile used as a sequential module	0.153	0.151	0.151
PAC5	First contribution of a VersaTile used as a sequential module	0.029	0.029	0.029
PAC6	Second contribution of a VersaTile used as a sequential module	0.323	0.323	0.323
PAC7	Contribution of a VersaTile used as a combinatorial module	0.280	0.300	0.278
PAC8	Average contribution of a routing net	1.097	1.081	1.130
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9.		
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-9.		
PAC11	Average contribution of a RAM block during a read operation	25.00		
PAC12	Average contribution of a RAM block during a write operation	30.00		
PAC13	Dynamic contribution for PLL	2.70		

Note: 1. There is no Center Global Rib present in AGLP030, and thus it starts directly at the spine resulting in 0μW/MHz.

Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices For IGLOO PLUS V2 or V5 Devices, 1.5 V Core Supply Voltage

Parameter	Definition	Device-Specific Static Power (mW)		
		AGLP125	AGLP060	AGLP030
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8		
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-7		
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7		
PDC4	Static PLL contribution	1.84 ¹		
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-12 on page 2-8		

Notes:

1. This is the minimum contribution of the PLL when operating at lowest frequency.
2. For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC software.

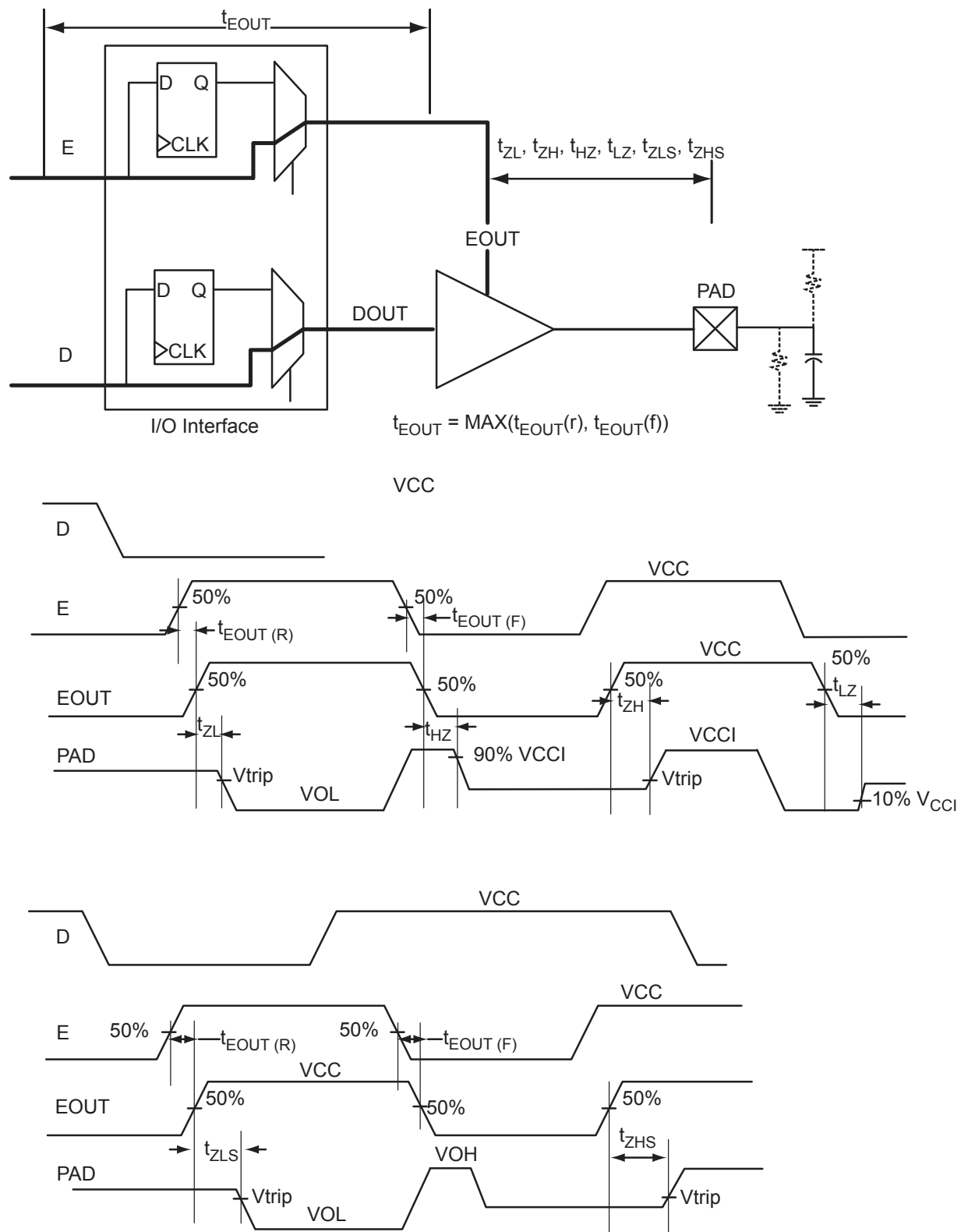


Figure 2-6 • Tristate Output Buffer Timing Model and Delays (example)

Table 2-24 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-39 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
4 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
6 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
8 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
12 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
16 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option ¹	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. μA^4	Max. μA^4	μA^5	μA^5
100 μA	2 mA	-0.3	0.8	2	3.6	0.2	$V_{DD} - 0.2$	100	100	25	27	10	10
100 μA	4 mA	-0.3	0.8	2	3.6	0.4	$V_{DD} - 0.2$	100	100	25	27	10	10
100 μA	6 mA	-0.3	0.8	2	3.6	0.4	$V_{DD} - 0.2$	100	100	51	54	10	10
100 μA	8 mA	-0.3	0.8	2	3.6	0.4	$V_{DD} - 0.2$	100	100	51	54	10	10
100 μA	12 mA	-0.3	0.8	2	3.6	0.4	$V_{DD} - 0.2$	100	100	103	109	10	10
100 μA	16 mA	-0.3	0.8	2	3.6	0.4	$V_{DD} - 0.2$	100	100	103	109	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

Note: *Measuring point = V_{trip} . See [Table 2-23 on page 2-20](#) for a complete table of trip points.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

Table 2-64 • Minimum and Maximum DC Input and Output Levels

1.2 V LVCMOS ¹	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. Applicable to IGLOO nano V2 devices operating at $VCCI \geq VCC$.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < V_{IN} < V_{IL}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

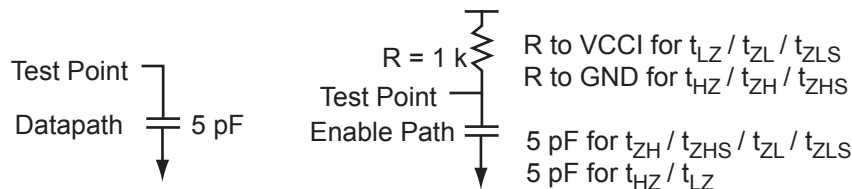


Figure 2-11 • AC Loading

Table 2-65 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-66 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	STD	0.98	8.27	0.19	1.57	2.34	0.67	7.94	6.77	3.00	3.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-67 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	STD	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.
2. Software default selection highlighted in gray.

Table 2-73 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t_{OERMCLR}	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
t_{ORECCLR}	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OECLR2Q}	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t_{OERMCLR}	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t_{OERECCLR}	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t_{IERMCLR}	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-13 on page 2-43 for more information.

Output Register

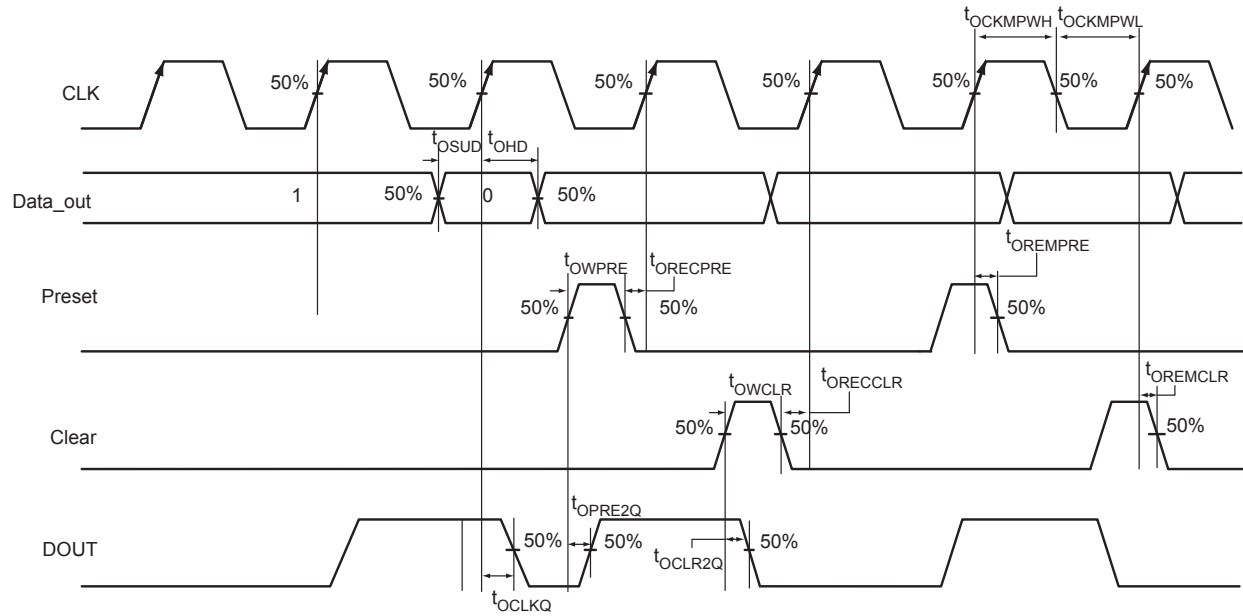


Figure 2-15 • Output Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-76 • Output Data Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.66	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.33	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.82	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.88	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-79 • Output Enable Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	1.06	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.52	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.25	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.36	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OEWPRES}$	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-90 • IGLOO PLUS CCC/PLL Specification
For IGLOO PLUS V2 or V5 devices, 1.5 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		250	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		250	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		360 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL ^{4, 5}			100	MHz
Input Cycle-to-Cycle Jitter (peak magnitude)			1	ns
Acquisition Time				
LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁶				
LockControl = 0			2.5	ns
LockControl = 1			1.5	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	1.25		15.65	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.469		15.65	ns
Delay Range in Block: Fixed Delay ^{1, 2}		3.5		ns
VCO Output Peak-to-Peak Period Jitter F_{CCC_OUT} ⁷	Maximum Peak-to-Peak Period Jitter ^{7, 8, 9}			
	SSO ≤ 2	SSO ≤ 4	SSO ≤ 8	SSO ≤ 16
0.75 MHz to 50 MHz	0.50%	0.60%	0.80%	1.20%
50 MHz to 250 MHz	2.50%	4.00%	6.00%	12.00%

Notes:

1. This delay is a function of voltage and temperature. See [Table 2-6 on page 2-6](#) and [Table 2-7 on page 2-6](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.5\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Maximum value obtained for a STD speed grade device in Worst Case Commercial Conditions. For specific junction temperature and voltage supply, refer to [Table 2-6 on page 2-6](#) and [Table 2-7 on page 2-6](#) for derating values.
5. The AGLP030 device does not support a PLL.
6. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.
7. VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the per cent jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps, regardless of the output divider settings.
8. Measurements done with LVTTTL 3.3 V 8 mA I/O drive strength and high slew rate, $V_{CC}/V_{CCPLL} = 1.425\text{ V}$, $V_{CCI} = 3.3\text{ V}$, VQ/PQ/TQ type of packages, 20 pF load.
9. SSO are outputs that are synchronous to a single clock domain and have clock-to-out times that are within $\pm 200\text{ ps}$ of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the [IGLOO PLUS FPGA Fabric User's Guide](#).

1.2 V DC Core Voltage

Table 2-94 • RAM4K9

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.25	ns
t_{ENH}	REN, WEN hold time	0.25	ns
t_{BKS}	BLK setup time	2.54	ns
t_{BKH}	BLK hold time	0.25	ns
t_{DS}	Input data (DIN) setup time	1.10	ns
t_{DH}	Input data (DIN) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	2.82	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.30	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.32	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.21	ns
	RESET Low to data out Low on DOUT (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

FF Flash*Freeze Mode Activation Pin

The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

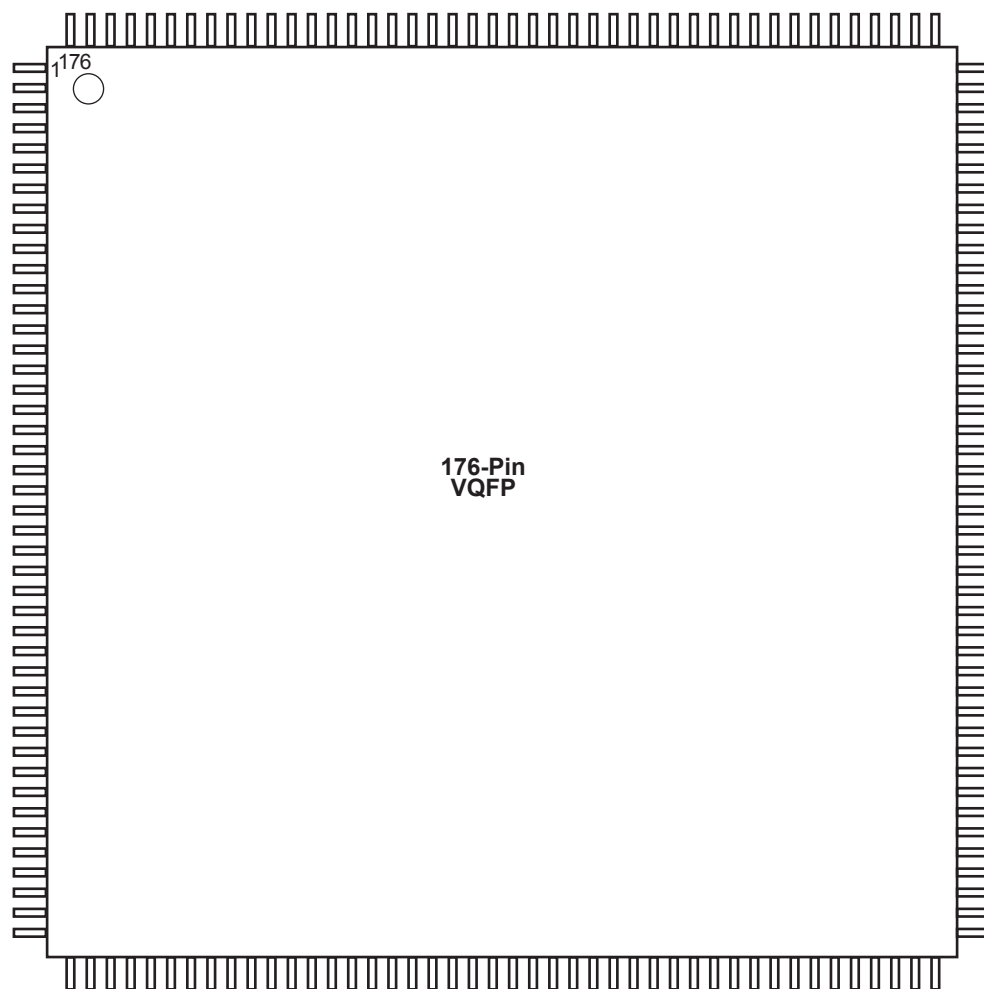
Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO and ProASIC3L devices. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO PLUS Device Family User's Guide* for more information on I/O states during Flash*Freeze mode.

Table 3-1 • Flash*Freeze Pin Location in IGLOO PLUS Devices

Package	Flash*Freeze Pin
CS281	W2
CS201	R4
CS289	U1
VQ128	34
VQ176	47

VQ128		VQ128		VQ128	
Pin Number	AGLP030 Function	Pin Number	AGLP030 Function	Pin Number	AGLP030 Function
1	IO119RSB3	36	IO88RSB2	71	IO57RSB1
2	IO118RSB3	37	IO86RSB2	72	VCCIB1
3	IO117RSB3	38	IO84RSB2	73	GND
4	IO115RSB3	39	IO83RSB2	74	IO55RSB1
5	IO116RSB3	40	GND	75	IO54RSB1
6	IO113RSB3	41	VCCIB2	76	IO53RSB1
7	IO114RSB3	42	IO82RSB2	77	IO52RSB1
8	GND	43	IO81RSB2	78	IO51RSB1
9	VCCIB3	44	IO79RSB2	79	IO50RSB1
10	IO112RSB3	45	IO78RSB2	80	IO49RSB1
11	IO111RSB3	46	IO77RSB2	81	VCC
12	IO110RSB3	47	IO75RSB2	82	GDB0/IO48RSB1
13	IO109RSB3	48	IO74RSB2	83	GDA0/IO47RSB1
14	GEC0/IO108RSB3	49	VCC	84	GDC0/IO46RSB1
15	GEA0/IO107RSB3	50	IO73RSB2	85	IO45RSB1
16	GEB0/IO106RSB3	51	IO72RSB2	86	IO44RSB1
17	VCC	52	IO70RSB2	87	IO43RSB1
18	IO104RSB3	53	IO69RSB2	88	IO42RSB1
19	IO103RSB3	54	IO68RSB2	89	VCCIB1
20	IO102RSB3	55	IO66RSB2	90	GND
21	IO101RSB3	56	IO65RSB2	91	IO40RSB1
22	IO100RSB3	57	GND	92	IO41RSB1
23	IO99RSB3	58	VCCIB2	93	IO39RSB1
24	GND	59	IO63RSB2	94	IO38RSB1
25	VCCIB3	60	IO61RSB2	95	IO37RSB1
26	IO97RSB3	61	IO59RSB2	96	IO36RSB1
27	IO98RSB3	62	TCK	97	IO35RSB0
28	IO95RSB3	63	TDI	98	IO34RSB0
29	IO96RSB3	64	TMS	99	IO33RSB0
30	IO94RSB3	65	VPUMP	100	IO32RSB0
31	IO93RSB3	66	TDO	101	IO30RSB0
32	IO92RSB3	67	TRST	102	IO28RSB0
33	IO91RSB2	68	IO58RSB1	103	IO27RSB0
34	FF/IO90RSB2	69	VJTAG	104	VCCIB0
35	IO89RSB2	70	IO56RSB1	105	GND

VQ176



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

CS201		CS201		CS201	
Pin Number	AGLP030 Function	Pin Number	AGLP030 Function	Pin Number	AGLP030 Function
A1	NC	C6	IO12RSB0	F3	IO119RSB3
A2	IO04RSB0	C7	IO23RSB0	F4	IO111RSB3
A3	IO06RSB0	C8	IO19RSB0	F6	GND
A4	IO09RSB0	C9	IO28RSB0	F7	VCC
A5	IO11RSB0	C10	IO32RSB0	F8	VCCIB0
A6	IO13RSB0	C11	IO35RSB0	F9	VCCIB0
A7	IO17RSB0	C12	NC	F10	VCCIB0
A8	IO18RSB0	C13	GND	F12	NC
A9	IO24RSB0	C14	IO41RSB1	F13	NC
A10	IO26RSB0	C15	IO37RSB1	F14	IO40RSB1
A11	IO27RSB0	D1	IO117RSB3	F15	IO38RSB1
A12	IO31RSB0	D2	IO118RSB3	G1	NC
A13	NC	D3	NC	G2	IO112RSB3
A14	NC	D4	GND	G3	IO110RSB3
A15	NC	D5	IO01RSB0	G4	IO109RSB3
B1	NC	D6	IO03RSB0	G6	VCCIB3
B2	NC	D7	IO10RSB0	G7	GND
B3	IO08RSB0	D8	IO21RSB0	G8	VCC
B4	IO05RSB0	D9	IO25RSB0	G9	GND
B5	IO07RSB0	D10	IO30RSB0	G10	GND
B6	IO15RSB0	D11	IO33RSB0	G12	NC
B7	IO14RSB0	D12	GND	G13	NC
B8	IO16RSB0	D13	NC	G14	IO42RSB1
B9	IO20RSB0	D14	IO36RSB1	G15	IO44RSB1
B10	IO22RSB0	D15	IO39RSB1	H1	NC
B11	IO34RSB0	E1	IO115RSB3	H2	GEB0/IO106RSB3
B12	IO29RSB0	E2	IO114RSB3	H3	GEC0/IO108RSB3
B13	NC	E3	NC	H4	NC
B14	NC	E4	NC	H6	VCCIB3
B15	NC	E12	NC	H7	GND
C1	NC	E13	NC	H8	VCC
C2	NC	E14	GDC0/IO46RSB1	H9	GND
C3	GND	E15	GDB0/IO48RSB1	H10	VCCIB1
C4	IO00RSB0	F1	IO113RSB3	H12	IO54RSB1
C5	IO02RSB0	F2	IO116RSB3	H13	GDA0/IO47RSB1

CS201	
Pin Number	AGLP060 Function
H14	IO64RSB1
H15	IO62RSB1
J1	GFA2/IO134RSB3
J2	GFA0/IO135RSB3
J3	GFB2/IO133RSB3
J4	IO131RSB3
J6	VCCIB3
J7	GND
J8	VCC
J9	GND
J10	VCCIB1
J12	IO61RSB1
J13	IO63RSB1
J14	IO68RSB1
J15	IO66RSB1
K1	IO130RSB3
K2	GFC2/IO132RSB3
K3	IO127RSB3
K4	IO129RSB3
K6	GND
K7	VCCIB2
K8	VCCIB2
K9	VCCIB2
K10	VCCIB1
K12	IO65RSB1
K13	IO67RSB1
K14	IO69RSB1
K15	IO70RSB1
L1	IO126RSB3
L2	IO128RSB3
L3	IO121RSB3
L4	IO123RSB3
L12	GDB1/IO74RSB1
L13	GDC1/IO72RSB1
L14	IO71RSB1

CS201	
Pin Number	AGLP060 Function
L15	GDC0/IO73RSB1
M1	IO122RSB3
M2	IO124RSB3
M3	IO119RSB3
M4	GND
M5	IO125RSB3
M6	IO98RSB2
M7	IO96RSB2
M8	IO91RSB2
M9	IO89RSB2
M10	IO82RSB2
M11	GDA2/IO78RSB2
M12	GND
M13	GDA1/IO76RSB1
M14	GDA0/IO77RSB1
M15	GDB0/IO75RSB1
N1	IO117RSB3
N2	IO120RSB3
N3	GND
N4	GEB1/IO114RSB3
N5	IO107RSB2
N6	IO100RSB2
N7	IO94RSB2
N8	IO87RSB2
N9	IO85RSB2
N10	GDC2/IO80RSB2
N11	IO90RSB2
N12	IO84RSB2
N13	GND
N14	TDO
N15	VJTAG
P1	GEC0/IO115RSB3
P2	GEC1/IO116RSB3
P3	GEA0/IO111RSB3
P4	GEA1/IO112RSB3

CS201	
Pin Number	AGLP060 Function
P5	IO106RSB2
P6	IO105RSB2
P7	IO103RSB2
P8	IO99RSB2
P9	IO93RSB2
P10	IO92RSB2
P11	IO95RSB2
P12	IO86RSB2
P13	IO83RSB2
P14	VPUMP
P15	TRST
R1	IO118RSB3
R2	GEB0/IO113RSB3
R3	GEA2/IO110RSB2
R4	FF/GEB2/IO109RSB2
R5	GEC2/IO108RSB2
R6	IO102RSB2
R7	IO101RSB2
R8	IO104RSB2
R9	IO97RSB2
R10	IO88RSB2
R11	IO81RSB2
R12	GDB2/IO79RSB2
R13	TMS
R14	TDI
R15	TCK

CS289	
Pin Number	AGLP030 Function
G10	GND
G11	GND
G12	IO40RSB1
G13	NC
G14	IO39RSB1
G15	IO44RSB1
G16	NC
G17	GND
H1	NC
H2	GEC0/IO108RSB3
H3	NC
H4	IO112RSB3
H5	NC
H6	IO109RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	NC
H13	NC
H14	IO45RSB1
H15	VCCIB1
H16	GDB0/IO48RSB1
H17	IO42RSB1
J1	NC
J2	GEA0/IO107RSB3
J3	VCCIB3
J4	IO105RSB3
J5	NC
J6	NC
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	IO50RSB1

CS289	
Pin Number	AGLP030 Function
J13	IO43RSB1
J14	IO51RSB1
J15	IO52RSB1
J16	GDC0/IO46RSB1
J17	GDA0/IO47RSB1
K1	GND
K2	GEB0/IO106RSB3
K3	IO102RSB3
K4	IO104RSB3
K5	IO99RSB3
K6	NC
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	NC
K13	NC
K14	NC
K15	IO53RSB1
K16	GND
K17	IO49RSB1
L1	IO103RSB3
L2	IO101RSB3
L3	NC
L4	GND
L5	NC
L6	NC
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	IO58RSB1
L13	IO54RSB1
L14	VCCIB1
L15	NC

CS289	
Pin Number	AGLP030 Function
L16	NC
L17	NC
M1	NC
M2	VCCIB3
M3	IO100RSB3
M4	IO98RSB3
M5	IO93RSB3
M6	IO97RSB3
M7	NC
M8	NC
M9	IO71RSB2
M10	NC
M11	IO63RSB2
M12	NC
M13	IO57RSB1
M14	NC
M15	NC
M16	NC
M17	VCCIB1
N1	NC
N2	NC
N3	IO95RSB3
N4	IO96RSB3
N5	GND
N6	NC
N7	IO85RSB2
N8	IO79RSB2
N9	IO77RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	IO59RSB2
N14	NC
N15	GND
N16	IO56RSB1
N17	IO55RSB1
P1	IO94RSB3

Revision	Changes	Page
Revision 11 (continued)	Table 2-2 • Recommended Operating Conditions ^{1,2} was revised. 1.2 V DC wide range supply voltage and 3.3 V wide range supply voltage (SAR 26270) were added for VCCI. VJTAG DC Voltage was revised (SAR 24052). The value range for VPUMP programming voltage for operation was changed from "0 to 3.45" to "0 to 3.6" (SAR 25220).	2-2
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to T _J = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to T _J = 70°C, VCC = 1.14 V) were revised.	2-6, 2-6
	Table 2-8 • Power Supply State per Mode is new.	2-7
	The tables in the "Quiescent Supply Current" section were updated (SARs 24882 and 24112). Some of the table notes were changed or deleted.	2-7
	VIH maximum values in tables were updated as needed to 3.6 V (SARs 20990, 79370).	N/A
	The values in the following tables were updated. 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added to the tables where applicable.	
	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings	2-9
	Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings ¹	2-9
	Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings	2-19
	Table 2-22 • Summary of Maximum and Minimum DC Input Levels	2-20
	Table 2-23 • Summary of AC Measuring Points	2-20
	Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade, Commercial-Case Conditions: T _J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V	2-22
	Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade Commercial-Case Conditions: T _J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V	2-23
	Table 2-28 • I/O Output Buffer Maximum Resistances ¹	2-24
	A table note was added to Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices stating the value for PDC4 is the minimum contribution of the PLL when operating at lowest frequency.	2-10, 2-11
	Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances was revised, including addition of 3.3 V and 1.2 V LVCMOS wide range. The notes defining R _{WEAK PULL-UP-MAX} and R _{WEAK PULLDOWN-MAX} were revised (SAR 21348).	2-25
	Table 2-30 • I/O Short Currents IOSH/IOSL was revised to include data for 3.3 V and 1.2 V LVCMOS wide range (SAR 79353 and SAR 79366).	2-25
	Table 2-31 • Duration of Short Circuit Event before Failure was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 26259).	2-26



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